Ultim® Extreme Silicon Drift Detector

Delivering solutions beyond conventional nano-analysis in the SEM



Ultim Extreme

Solutions beyond conventional nanoanalysis in the FEG-SEM...



Analysis of a bulk cross section of a smart phone SRAM device: the EDS X-ray map resolution approaches that of the SEM image. Data courtesy of MSS Corp.

A spatial resolution and sensitivity breakthrough for EDS in the FEG-SEM

Ultra-high resolution FEG-SEMs offer exciting new capabilities for the investigation of smaller nano-structures, interfaces and surfaces. However, under the operating conditions used to make use of new electron signal contrasts from in-lens detectors - very short working distance, very low kV and minimal beam current - no traditional SDD can provide supporting elemental characterisation.

Until now. With **Ultim** Extreme, both imaging and EDS are performed simultaneously, while the EDS resolution approaches that of the SEM itself. Radical new geometry maximises sensitivity and spatial resolution in FEG/FIB-SEM:

- Highest sensitivity conventional port-mounted EDS detector
- Windowless operation
- Typically 15 x greater sensitivity at low kV than conventional large area SDD
- Unique shape 100 mm² sensor for short working distance operation
- Reduced footprint electron trap configuration allows qualitative analysis up to 7 kV beam voltage
- Use immersion field to extend quantitative range up to 15kV and beyond

- New electronics boost sensitivity to very low energy X-rays and extends the low energy analytical performance at higher count rates
- Enhanced Tru-Q[™] software turns the X-ray data into practical and accurate elemental information at this unrivalled spatial resolution

EDS resolution approaches that of the FEG-SEM ...new possibilities, better spatial resolution, more sensitivity



Reducing accelerating voltage from 10kV to 1.5kV allows electron image contrast to show the distribution of oxide particles. X-ray mapping under the same conditions characterises precipitates as MnOB.

X-ray map collected at 1 kV to characterise high-end electronic component stain detected using In-lens SE imaging.

Sub 10nm element characterisation

Achieving practical EDS count rates and spectral quality at 2 kV or less, combined with short working distance for optimum beam size means unrivalled spatial resolution for element characterisation is now possible:

- Practical sub 10 nm element characterisation on real materials in the FEG/FIB-SEM
- X-ray map resolution close to SEM image resolution
- Characterise smaller nanostructures, particles and materials
- Use bulk samples to reduce workload on TEM and sample preparation time

Materials characterisation down to 1kV

The latest in-lens detectors provide new types of image contrast for new information about nano-structures. **Ultim** Extreme works at the same collection conditions to add elemental information to this new image information.

- Fully integrate EDS where very low kV electron microscopy benefits sample characterisation
- Enhanced signal contrast
- Reduction of sample damage e.g. for polymers and soft coatings
- Reduce charging, or achieve charge balance conditions

Surface science sensitivity

At very low accelerating voltages, X-ray information is emitted from the top few nm or atomic layers only, making the elemental characterisation of surfaces in the FEG/FIB-SEM possible:

- Characterise the composition and distribution of surface contaminants and layers a few atoms thick
- Integrate characterisation of surfaces with SEM investigation
- Analyse the surface structures only visible with in-lens detectors at very low kV and short working distance
- Save money and time compared to Auger/XPS

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Spectrum collected from LiAlO grain in a LiLaZrAlO solid battery electrolyte.

Fastest and most accurate nano-characterisation

Ultim Extreme collects more and better quality EDS data at higher spatial resolution. With the **AZtec** Tru-Q[™] processing engine, this provides the fastest, most accurate characterisation possible in the FEG/FIB-SEM.

- High speed collection
- Unrivalled low energy spectrum quality and integrity
- Real-time data processing
- Rapid autoID and TruMap peak overlap correction of low energy X-ray lines

Extreme light element sensitivity

The windowless configuration and ultra high sensitivity of **Ultim** Extreme offers the most sensitive light element detection.

- Up to 15 x increase in signal over conventional detectors
- Work at lower kV to minimise sample damage and charging
- New potential for the detection and characterisation of difficult elements, such as nitrogen
- New ability to analyse polymers and soft biological materials

EDS map of solid electrolyte showing LiKα mapping (yellow)

Lithium detection and mapping

Oxford Instruments announced the first successful detection of Li X-rays by EDS in 2012. We have developed this know-how adding new ultra low noise electronics for the detection of X-rays below 100 eV.

- First detection and X-ray mapping of Li Kα (only 56 eV)
- First detection of lithium in compounds e.g. LiH, Li₃N, Li₂O, Li₂S, LiF and LiCl by EDS
- First characterisation of Li in battery materials

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